

not a limitation. The term "solely" is the only added term that achieves the desired result of minimizing the parasitic capacitance, which result was always intended by this claim.

Proposed amended claim 1

1 (Currently amended). An organic field effect transistor (OFET) including a gate, comprising:

a first electrode layer forming source and drain electrodes each having multiple sides ;

a semiconducting layer;

an insulator layer;

one of the source and drain electrodes in the first electrode layer surrounding the respective other electrode of the first electrode layer in a two-dimensional manner with the exception of one of said sides of the other electrode ; and

a second electrode layer forming a gate electrode, the semiconducting layer exhibiting a current channel in the presence of an applied voltage and wherein the second electrode layer completely overlies the current channel and overlies a portion of the source or drain electrodes of the first electrode layer, the overlying portion with respect to the source or drain electrodes having a width solely in the range from about 0 to about 20 μ m and having a length in the range of the length of the current channel;

whereby a u-shaped and/or meandering current channel , which begins and ends on one of said sides of the electrode of the first electrode layer is formed in the semiconducting layer to thereby minimize parasitic capacitance that otherwise might be present.

VIA FACSIMILE TO THE USPTO

I hereby certify that this paper is being sent by facsimile to Examiner Swapneel Chhaya, Art Unit 2822 USPTO on the date indicated below, at facsimile no. 571 270 2434.


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